

<b>Notice of References Cited</b>	Application/Control No. 10/591,456		Applicant(s)/Patent Under Reexamination OGURA ET AL.	
	Examiner JESSE A. ELBIN		Art Unit 2614	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-4,142,073	02-1979	Agneus et al.	381/174
*	B	US-2002/0181725	12-2002	Johannsen et al.	381/174
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	T. Majamaa et al., Effect of Oxidation Temperature on the Electrical Characteristics of Ultrathin Silicon Dioxide Layers Plasma Oxidized in Ultrahigh Vacuum, 1999, Physica Scripta, Vol. T79, 259-262.
	V	E.C.Ross et al., Effects of Silicon Nitride Growth Temperature on Charge Storage in the MNOS Structure, 1969, Applied Physics Letters, Volume 15 Number 12, 408-409.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.